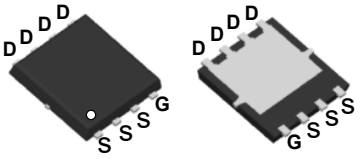
WMB100N07TS

70V N-Channel Enhancement Mode Power MOSFET

Description

WMB100N07TS uses advanced power trench technology that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

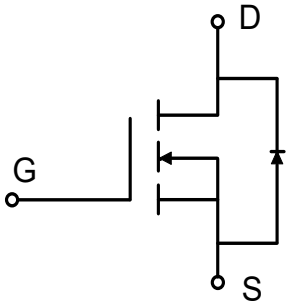


PDFN5060-8L

Features

- V_{DS}= 70V, I_D = 100A
  $R_{DS(on)}$ < 7.4mΩ @ V_{GS} = 10V
- Green Device Available
- Low Gate Charge
- Advanced High Cell Density Trench Technology
- 100% EAS Guaranteed

RoHS compliant



Applications

- Synchronous Rectification
- DC/DC Converter
- Motor Control

Absolute Maximum Ratings（Tc = 25°C, unless otherwise noted）

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	70	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_C=25°C	I_D	100	A
	T_C=100°C		63	
Pulsed Drain Current[4]		I_{DM}	400	A
Single Pulse Avalanche Energy[3]		EAS	217.8	mJ
Total Power Dissipation	T_C=25°C	P_D	125	W
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance from Junction-to-Ambient[1]	$R_{\theta JA}$	42	°C/W
Thermal Resistance from Junction-to-Case	$R_{\theta JC}$	1	°C/W

Electrical Characteristics（Tc = 25°C, unless otherwise noted）

Parameter		Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics							
Drain-Source Breakdown Voltage		$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	70	-	-	V
Gate-body Leakage current		I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V	-	-	±100	nA
Zero Gate Voltage Drain Current	T_J=25°C	I_{DSS}	V_{DS} =70V, V_{GS} = 0V	-	-	1	μA
	T_J=55°C			-	-	100	
Gate-Threshold Voltage		$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	2	3	4	V
Drain-Source on-Resistance[2]		$R_{DS(on)}$	V_{GS} = 10V, I_D = 20A	-	5.6	7.4	mΩ
Forward Transconductance[2]		g_{fs}	V_{DS}=5V , I_D=20A	-	76	-	S
Dynamic Characteristics							
Input Capacitance		C_{iss}	V_{DS} = 35V, V_{GS} =0V, f =1MHz	-	4030	-	pF
Output Capacitance		C_{oss}		-	271	-	
Reverse Transfer Capacitance		C_{rss}		-	189	-	
Switching Characteristics							
Gate Resistance		R_g	V_{DS} = 0V, V_{GS} =0V, f =1MHz	-	1.2	-	Ω
Total Gate Charge(10V)		Q_g	V_{GS} = 10V, V_{DS} = 35V, I_D=20A	-	92	-	nC
Gate-Source Charge		Q_{gs}		-	22	-	
Gate-Drain Charge		Q_{gd}		-	31	-	
Turn-On Delay Time		$t_{d(on)}$	V_{GS} =10V, V_{DD} =35V, R_G = 4.7Ω, I_D= 20A	-	36	-	ns
Rise Time		t_r		-	77	-	
Turn-Off Delay Time		$t_{d(off)}$		-	92	-	
Fall Time		t_f		-	34	-	
Drain-Source Body Diode Characteristics							
Diode Forward Voltage[2]		V_{SD}	I_S = 1A, V_{GS} = 0V	-	-	1	V
Continuous Source Current[1,5]		I_S	V_G=V_D=0V, Force Current	-	-	100	A

Notes:

1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.

2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.

3.The EAS data shows Max. rating . The test condition is V_{DD}=40V,V_{GS}=10V, L=0.4mH, I_{AS}=33A.

4.Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C.

5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

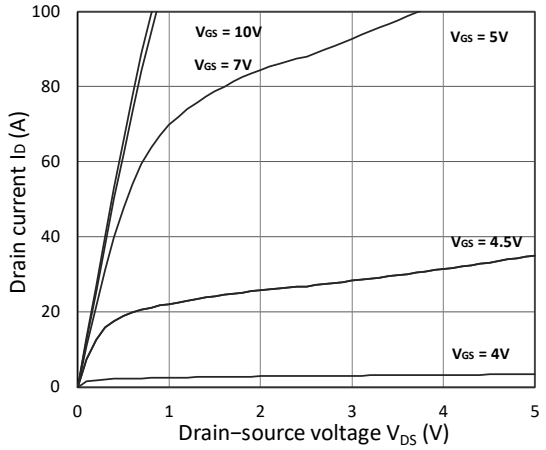


Figure 1. Output Characteristics

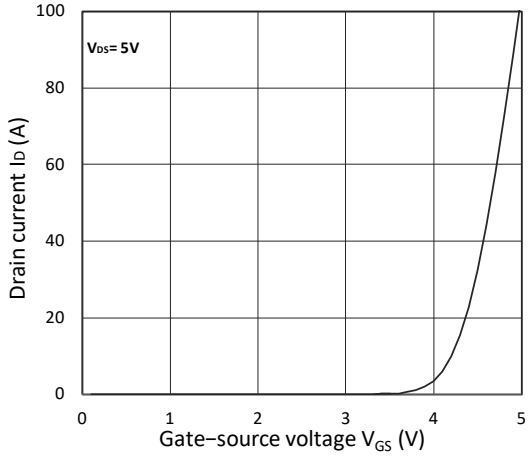


Figure 2. Transfer Characteristics

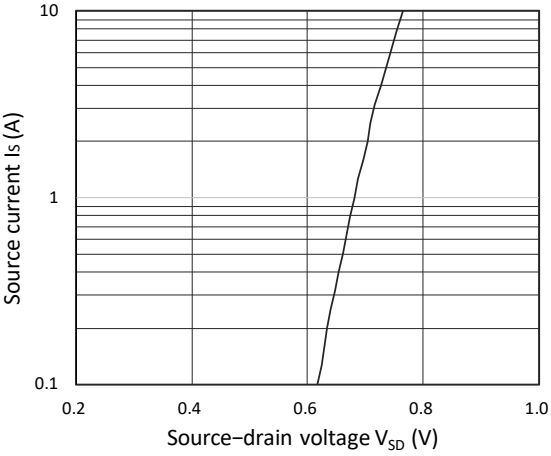


Figure 3. Forward Characteristics of Reverse

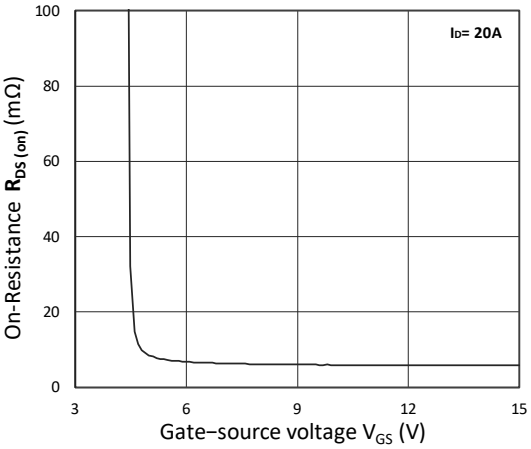


Figure 4. $R_{DS(ON)}$ vs. V_{GS}

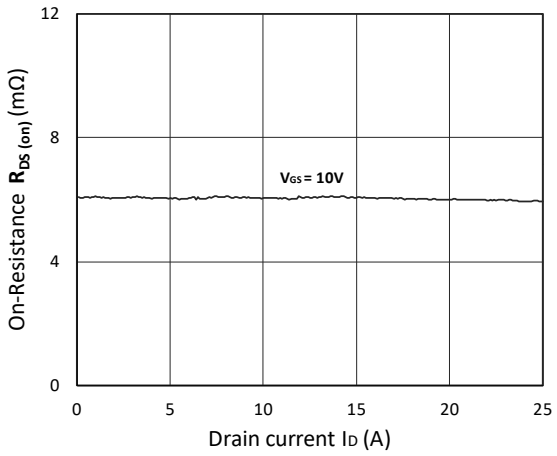


Figure 5. $R_{DS(ON)}$ vs. I_D

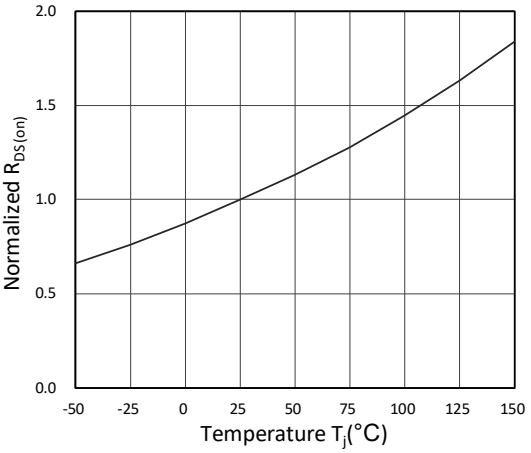


Figure 6. Normalized $R_{DS(on)}$ vs. Temperature

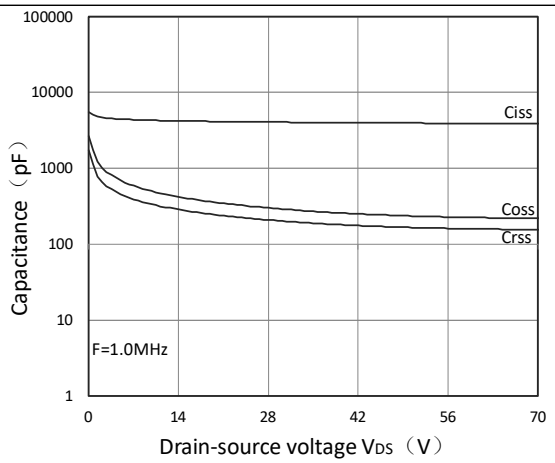


Figure 7. Capacitance Characteristics

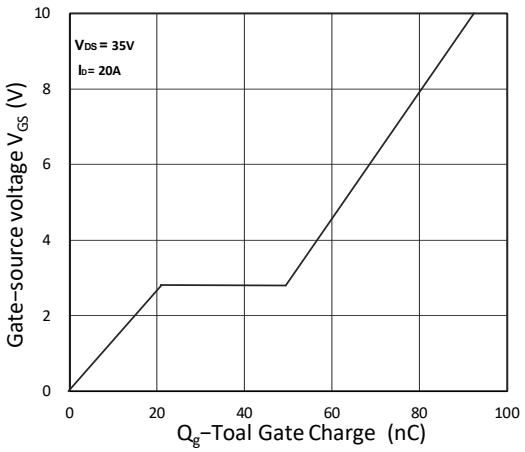


Figure 8. Gate Charge Characteristics

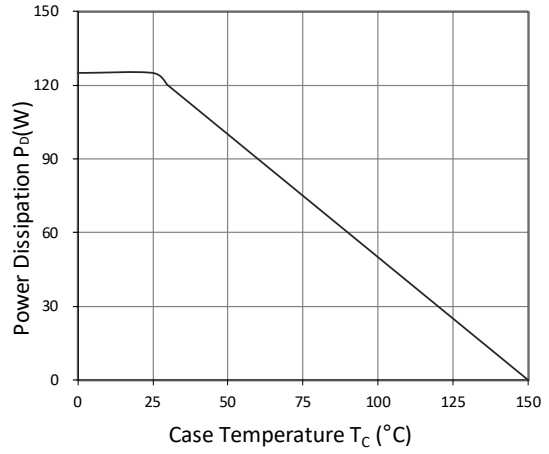


Figure 9. Power Dissipation

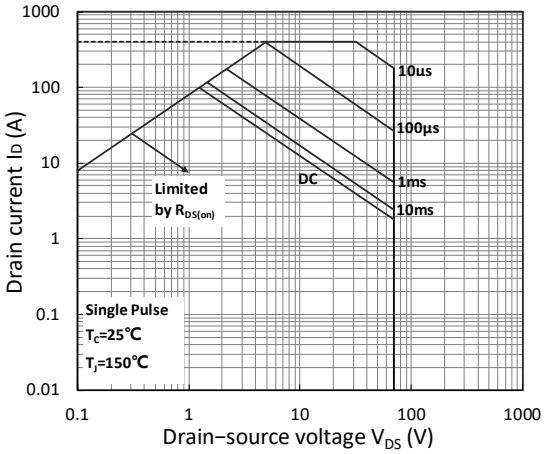


Figure10. Safe Operating Area

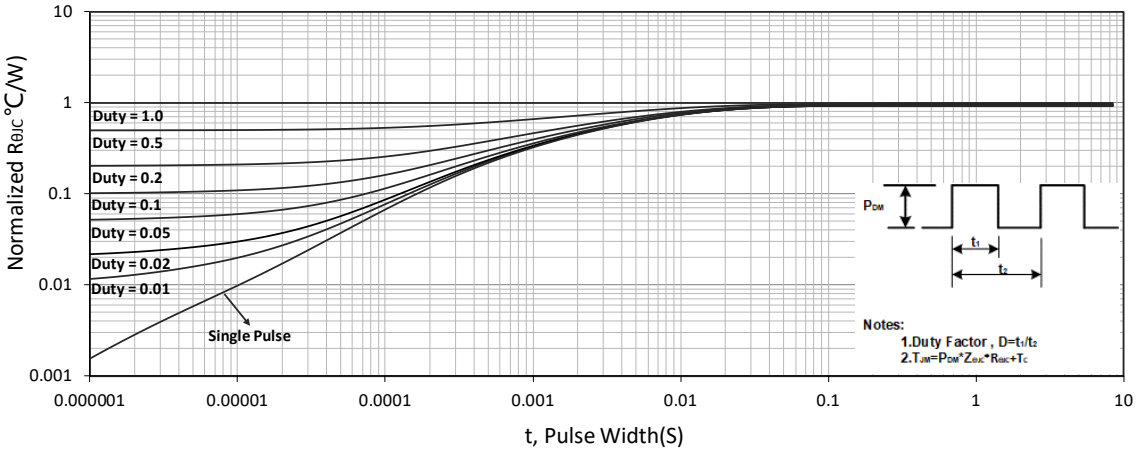


Figure 11. Normalized Maximum Transient Thermal Impedance

Test Circuit

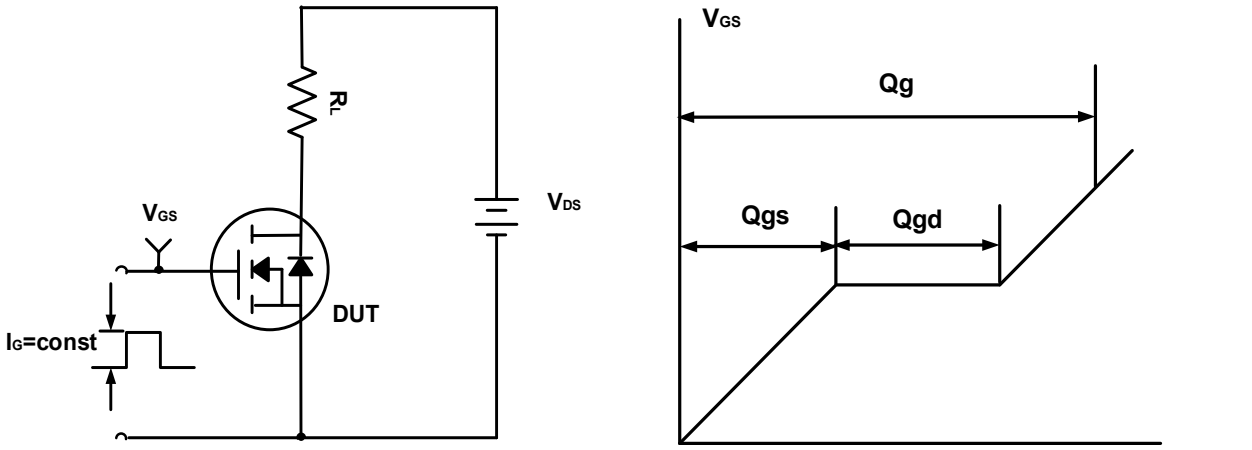


Figure A. Gate Charge Test Circuit & Waveforms

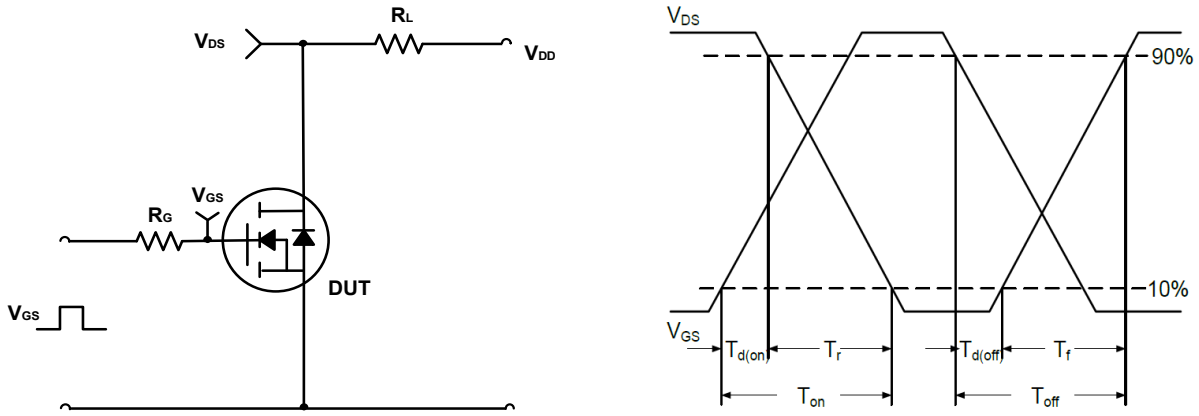


Figure B. Switching Test Circuit & Waveforms

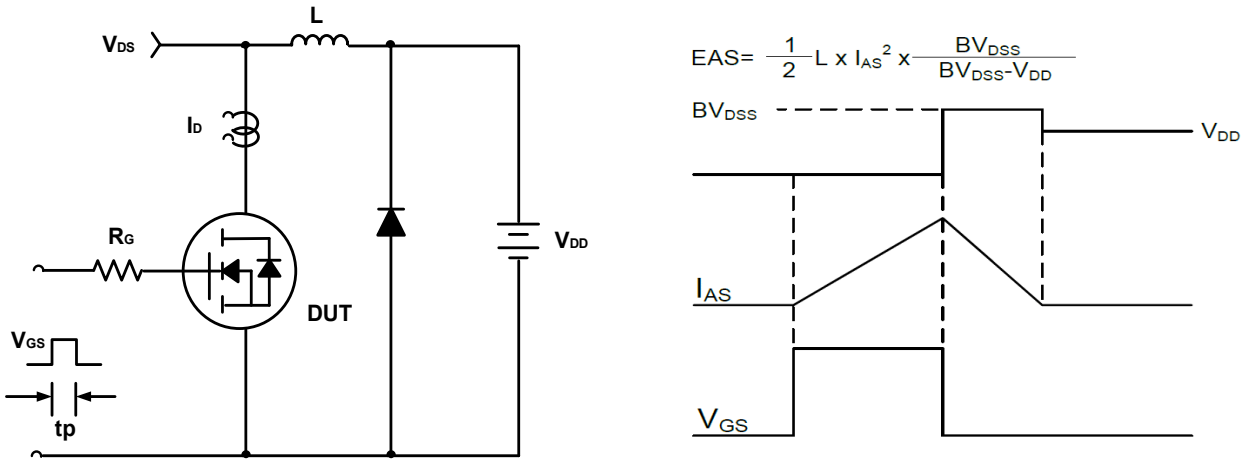
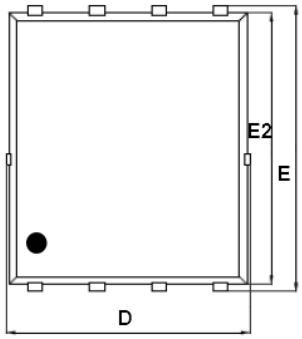
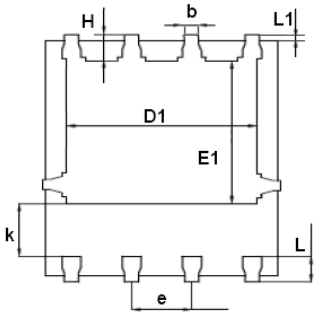
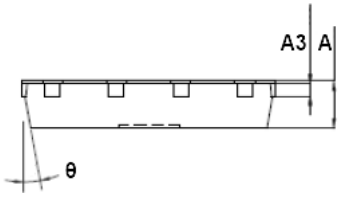


Figure C. Unclamped Inductive Switching Circuit & Waveforms

Mechanical Dimensions for PDFN5060-8L







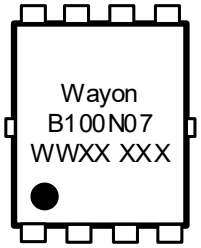
COMMON DIMENSIONS

SYMBOL	MM	
	MIN	MAX
A	0.90	1.20
A3	0.15	0.35
D	4.80	5.40
E	5.90	6.35
D1	3.61	4.31
E1	3.30	3.92
E2	5.50	6.06
k	1.10	-
b	0.30	0.51
e	1.27BSC	
L	0.38	0.71
L1	0.05	0.36
H	0.38	0.71
θ	0°	12°

Ordering Information

Part	Package	Marking	Packing method
WMB100N07TS	PDFN5060-8L	B100N07	Tape and Reel

Marking Information



B100N07 = Device code

WWXX XXX= Date code

Contact Information

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WAYON website: **http://www.way-on.com**
For additional information, please contact your local Sales Representative.

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